Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

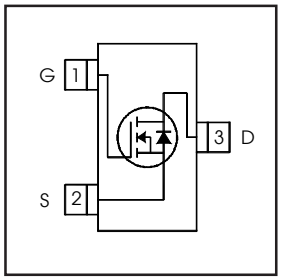
International
IOR Rectifier

PD - 96163A

IRLML2502GPbF

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free
- Halogen-Free



V_{DSS} = 20V

$R_{DS(on)}$ = 0.045Ω

Description

These N-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.

Micro3™

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 4.5V	4.2	A
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ 4.5V	3.4	
I_{DM}	Pulsed Drain Current ①	33	
P_D @T_A = 25°C	Power Dissipation	1.25	W
P_D @T_A = 70°C	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

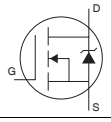
09/25/12

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	V_{GS} = 0V, I_D = 250uA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.035	0.045	Ω	V_{GS} = 4.5V, I_D = 4.2A ②
		—	0.050	0.080		V_{GS} = 2.5V, I_D = 3.6A ②
$V_{GS(th)}$	Gate Threshold Voltage	0.60	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-3.2	—	mV/°C	
gfs	Forward Transconductance	5.8	—	—	S	V_{DS} = 10V, I_D = 4.0A
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	µA	V_{DS} = 16V, V_{GS} = 0V
		—	—	25		V_{DS} = 16V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -12V
Q_g	Total Gate Charge	—	8.0	12	nC	I_D = 4.0A
Q_{gs}	Gate-to-Source Charge	—	1.8	2.7		V_{DS} = 10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.7	2.6		V_{GS} = 5.0V ②
$t_{d(on)}$	Turn-On Delay Time	—	7.5	—	ns	V_{DD} = 10V
t_r	Rise Time	—	10	—		I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	54	—		R_G = 6Ω
t_f	Fall Time	—	26	—		R_D = 10Ω ②
C_{iss}	Input Capacitance	—	740	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	90	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	66	—		f = 1.0MHz

Source-Drain Rating and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	33		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	T_J = 25°C, I_S = 1.3A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	16	24	ns	T_J = 25°C, I_F = 1.3A
Q_{rr}	Reverse Recovery Charge	—	8.6	13	nC	di/dt = 100A/µs ②



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Pulse width ≤ 300µs; duty cycle ≤ 2%.

③ Surface mounted on FR-4 board, t ≤ 5sec.

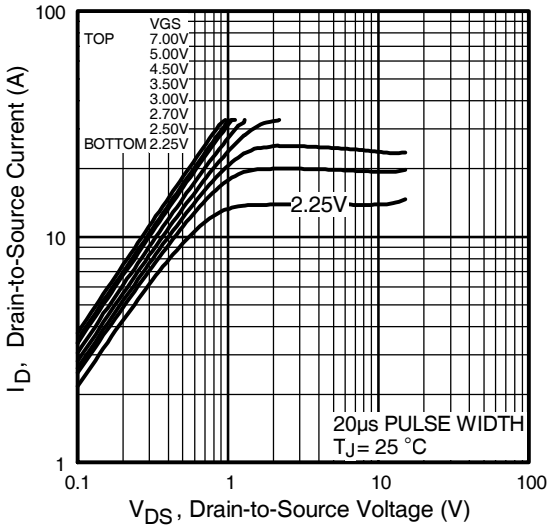


Fig 1. Typical Output Characteristics

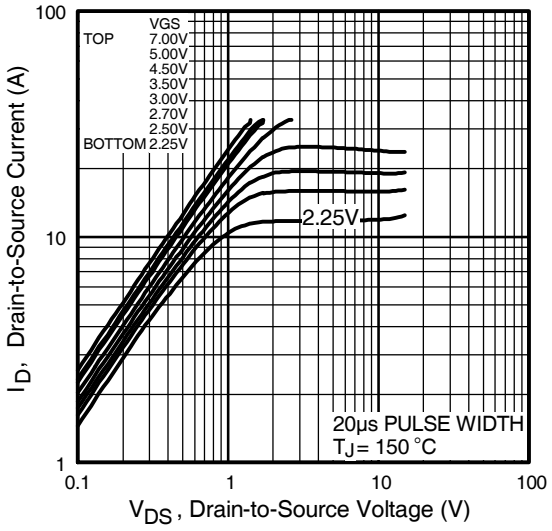


Fig 2. Typical Output Characteristics

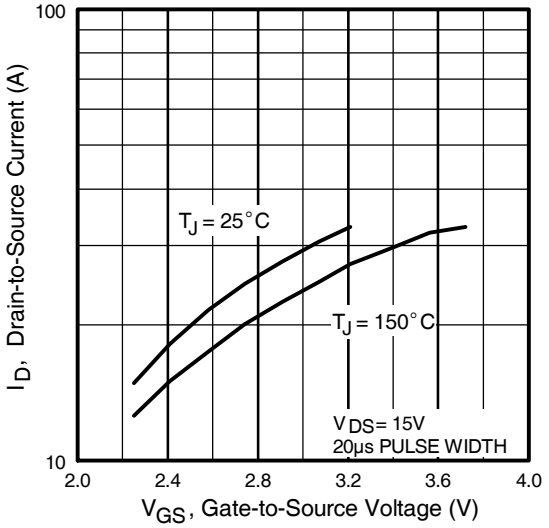


Fig 3. Typical Transfer Characteristics

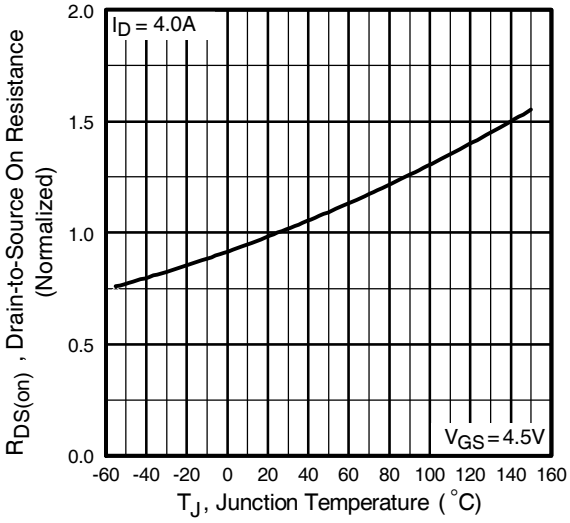


Fig 4. Normalized On-Resistance Vs. Temperature

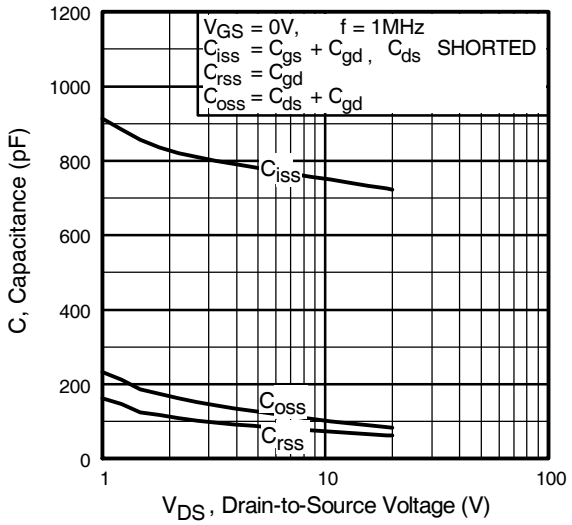


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

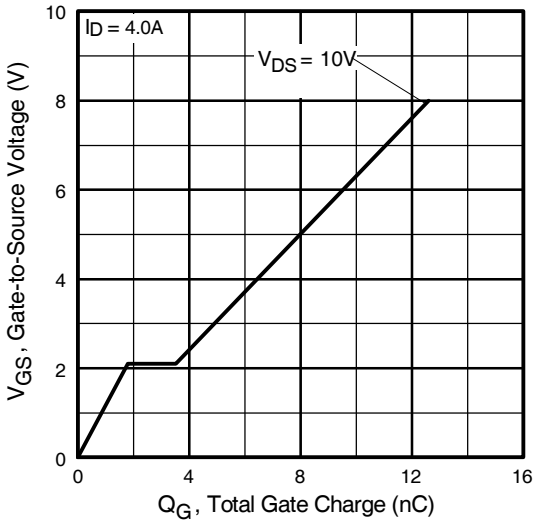


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

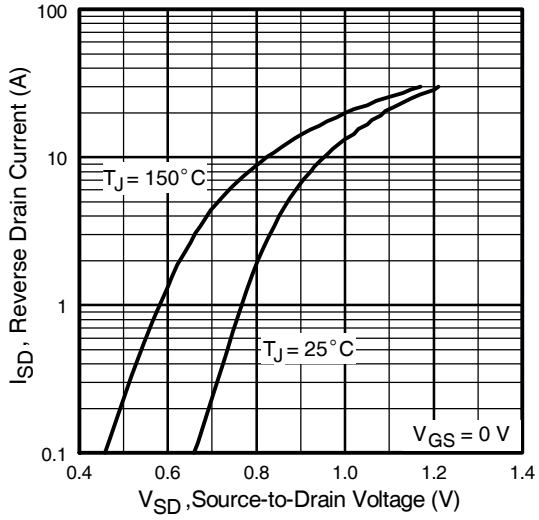


Fig 7. Typical Source-Drain Diode Forward Voltage

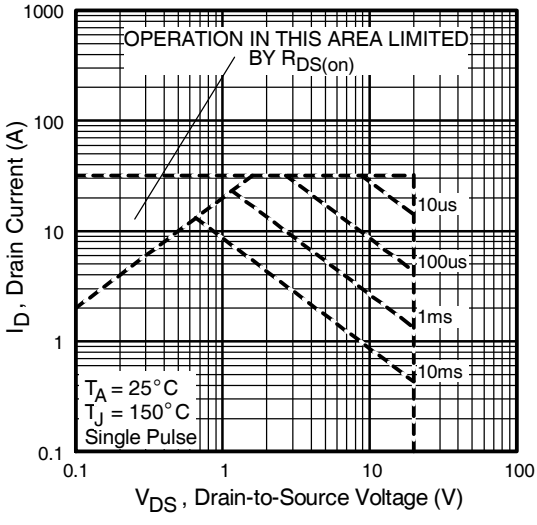


Fig 8. Maximum Safe Operating Area

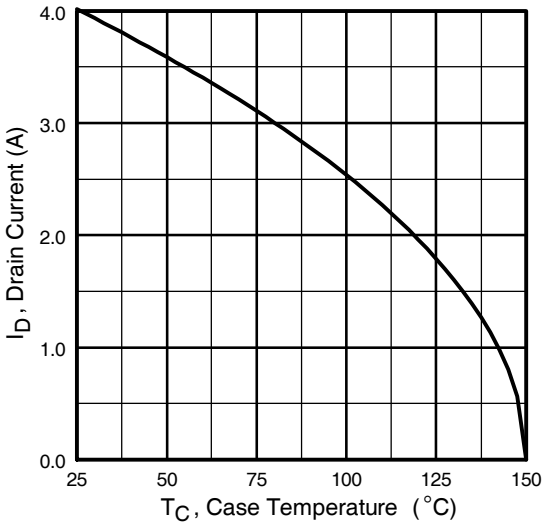


Fig 9. Maximum Drain Current Vs. Case Temperature

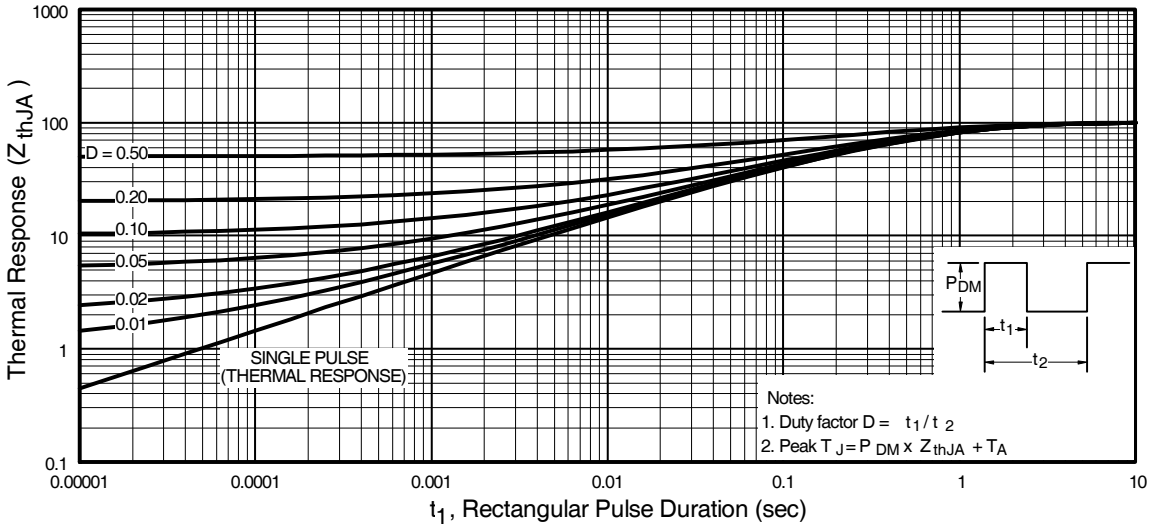


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

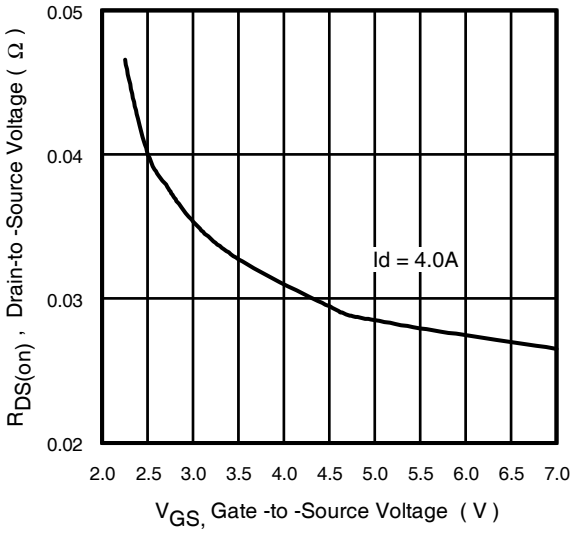


Fig 11. On-Resistance Vs. Gate Voltage

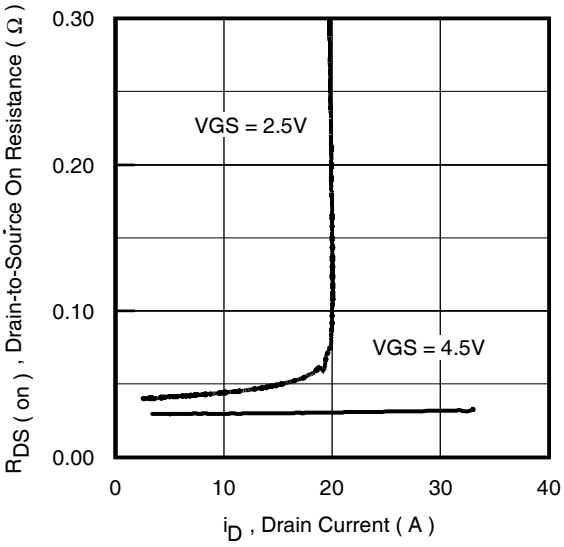


Fig 12. On-Resistance Vs. Drain Current

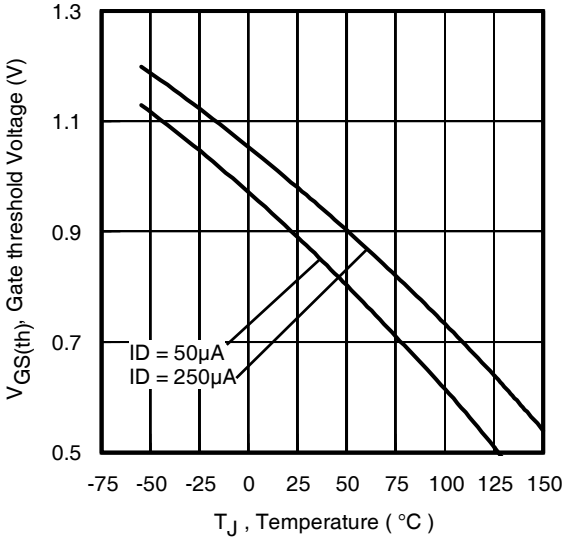
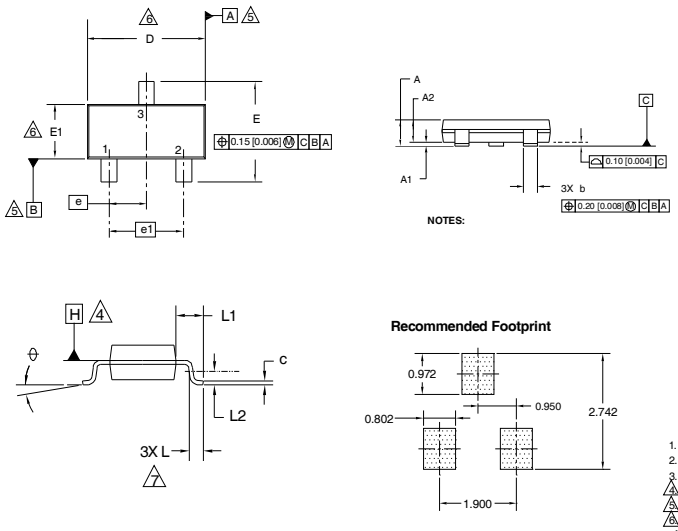


Fig 13. Threshold Voltage Vs. Temperature

Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)

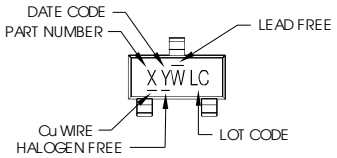


DIMENSIONS				
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	0.035	0.044
A1	0.01	0.10	0.0004	0.004
A2	0.88	1.02	0.035	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95	BSC	0.037	BSC
e1	1.90	BSC	0.075	BSC
L	0.40	0.60	0.016	0.024
L1	0.54	REF	0.021	REF
L2	0.25	BSC	0.010	BSC
θ	0	8	0	8

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM [0.010 INCH] PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001



X = PART NUMBER CODE REFERENCE:

A = IRLML2402
B = IRLML2803
C = IRLML6302
D = IRLML5103
E = IRLML6402
F = IRLML6401
G = IRLML2502
H = IRLML5203
I = IRLML0030
J = IRLML2030
K = IRLML0100
L = IRLML0060
M = IRLML0040
N = IRLML2060
P = IRLML9301
R = IRLML9303

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

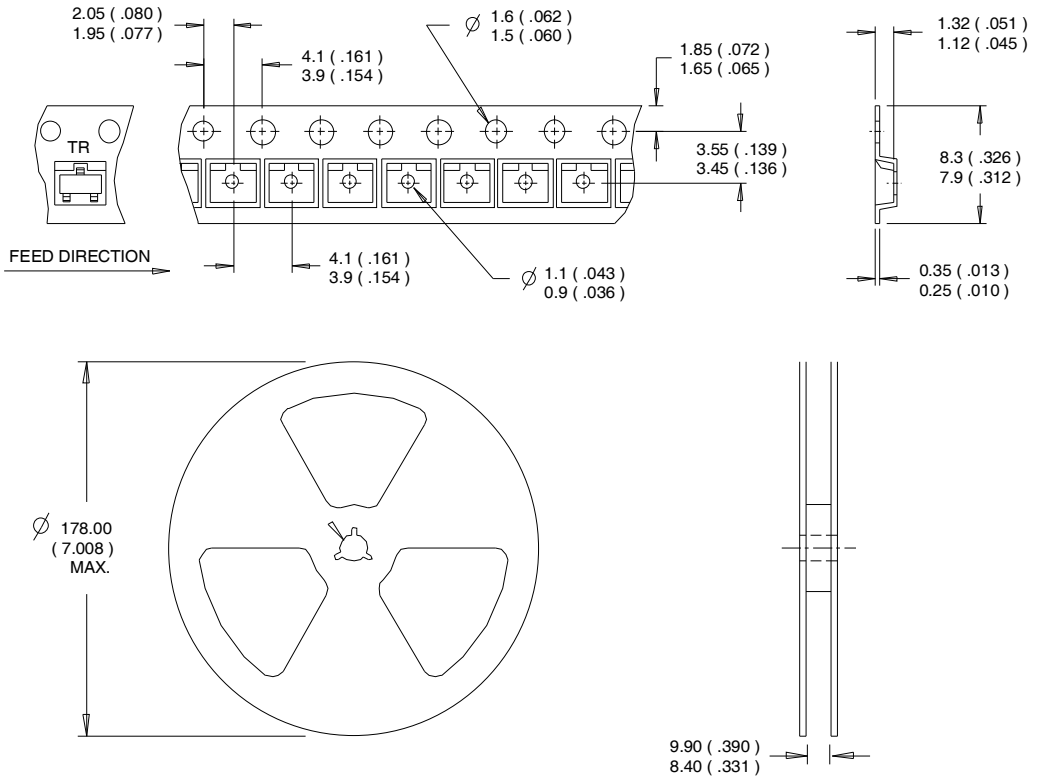
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package

Data and specifications subject to change without notice.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 101N.Sepulveda blvd, El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information. 09/2012